

MG25N1ZS1 Transistors

Independent IGBT Power Module

Isolated Case (Y/N) Yes

Circuits Per Package 1

$V(BR)_{CES}$ (V) 1.0k

$V(BR)_{GES}$ (V)

$I(C)$ Max. (A) 25

Absolute Max. Power Diss. (W) 200

Minimum Operating Temp ($\circ C$)

Maximum Operating Temp ($\circ C$)

Thermal Resistance Junc-Case

$I(CES)$ Min. (A)

@ $V(CES)$ (V) (Test Condition)

$I(GES)$ Max. (A)

@ $V(GES)$ (V) (Test Condition)

$V(CE)_{sat}$ Max. (V) 5.0

@ $I(C)$ (A) (Test Condition)

@ $V(GE)$ (Test Condition)

$V(GE)_{th}$ Max. (V)

@ $I(C)$ (A) (Test Condition)

@ $V(CE)$ (V) (Test Condition)

$g(fe)$ Min. (S) Trans. admitt.

$q(fe)$ Max. (S) Trans. admitt.